

Shottky barrier diode

RSX201L-30

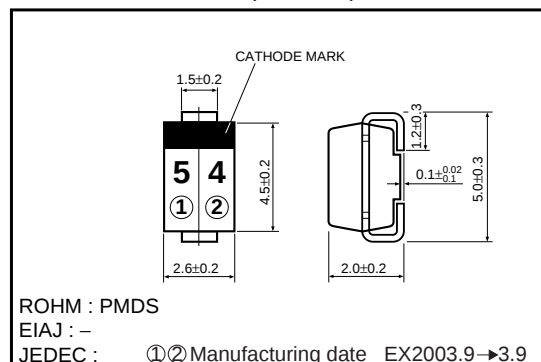
●Application

High efficient shottky barrier diode.
Rectifier for power supply units.
Battery protection against reversal current

●Features

- 1) Small mold type power diode (PMDS (4526))
- 2) High reliability
(ESD resistance typ=22kV (machine model))
- 3) Low V_F / Low I_R
($V_F=0.39V$ at $2A$ / $I_R=50\mu A$ at $30V$)

●External dimensions (Unit : mm)



●Structure

Silicon Epitaxial Planer

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	2	A
Forward peak surge current (60Hz / 1cyc.)	I_{FSM}	60	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 to 150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.39	0.44	V	$I_F=2A$
Reverse current	I_R	-	50	150	μA	$V_R=30V$
Capacitance between terminals	C_T	-	120	-	pF	$V_R=10V$, $f=1MHz$
Electro static discharge resistance	ESD	-	22	-	kV	$C=200pF$, $R=0\Omega$ 1pulse

Diodes

●Electrical characteristic curves (Ta=25°C)

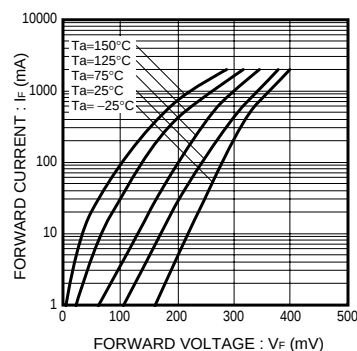


Fig.1 Forward Temperature Characteristics

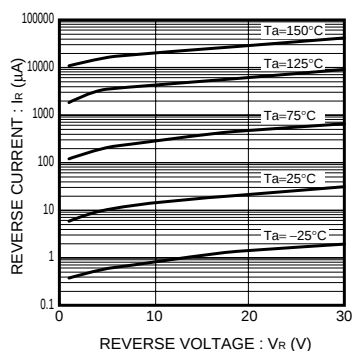


Fig.2 Reverse Temperature Characteristics

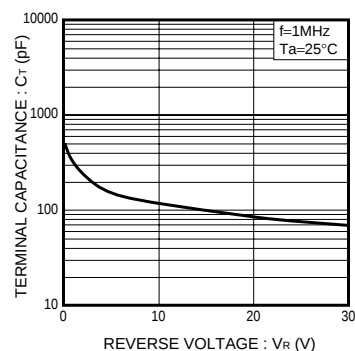


Fig.3 Capacitance Between Terminals Characteristics

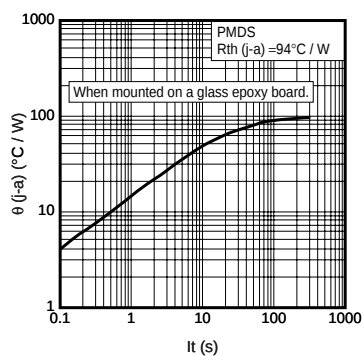


Fig.4 Thermal resistance

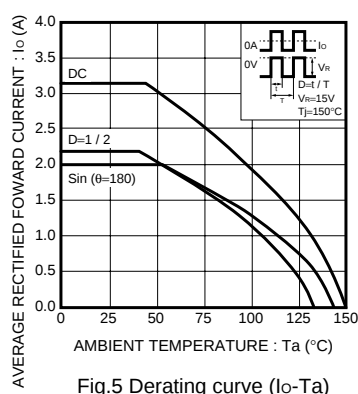


Fig.5 Derating curve (Io-Ta)

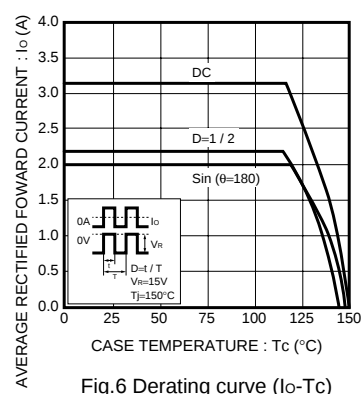


Fig.6 Derating curve (Io-Tc)

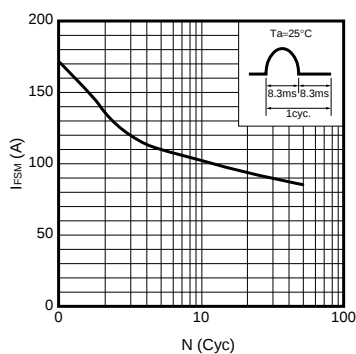


Fig.7 Forward peak surge current (Actual data)

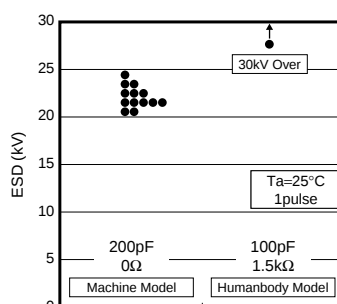


Fig.8 ESD resistance